Silicon PNP Power Transistors 2N5613 2N5615 2N5617 2N5619

DESCRIPTION

- With TO-3 package
- Excellent safe operating area
- Low collector saturation voltage

APPLICATIONS

- For general-purpose amplifier ; and switching applications

Fig.1 simplified outline (TO-3) and symbol

PINNING(see Fig.2)

PIN	DESCRIPTION
1	Base
2	Emitter
3	Collector

Absolute maximum ratings(Ta=℃)

SYMBOL	PARAMETER		CONDITIONS	VALUE	UNIT
V_{CBO}	Collector-base voltage	2N5613	Open emitter	-80	V
		2N5615/5617		-100	
		2N5619		-120	
V_{CEO}	Collector-emitter voltage	2N5613	Open base	-60	V
		2N5615/5617		-80	
		2N5619		-100	
V_{EBO}	Emitter-base voltage		Open collector	-5	V
I_C	Collector current			-5	A
P_D	Total power dissipation		T_C=25℃	50	W
T_j	Junction temperature			150	℃
T_{stg}	Storage temperature			-65~150	℃

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	VALUE	UNIT
$R_{th\ j\text{-}c}$	Thermal resistance junction to case	1.5	℃/W

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CHARACTERISTICS

Tj=25℃ unless otherwise specified

SYMBOL	PARAMETER		CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{CEO(SUS)}$	Collector-emitter sustaining voltage	2N5613	I_C=-50mA ;I_B=0	-60			V
		2N5615/5617		-80			
		2N5619		-100			
V_{CEsat}	Collector-emitter saturation voltage		I_C=-1A; I_B=-0.1A			-0.5	V
V_{BE}	Base-emitter on voltage		I_C=-2.5A ; V_{CE}=-5V			-1.5	V
I_{CBO}	Collector cut-off current		V_{CB}=Rated V_{CBO}; I_E=0			-0.1	mA
I_{CEO}	Collector cut-off current		V_{CE}= Rated V_{CEO},I_B=0			-1.0	mA
I_{EBO}	Emitter cut-off current		V_{EB}=-5V; I_C=0			-0.1	mA
h_{FE}	DC current gain	2N5613/5617	I_C=-2.5A ; V_{CE}=-5V	70		200	
		2N5615/5619		30		90	
f_T	Transition frequency	2N5613/5617	I_C=-0.5A ; V_{CE}=-10V	70			MHz
		2N5615/5619		60			

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PACKAGE OUTLINE

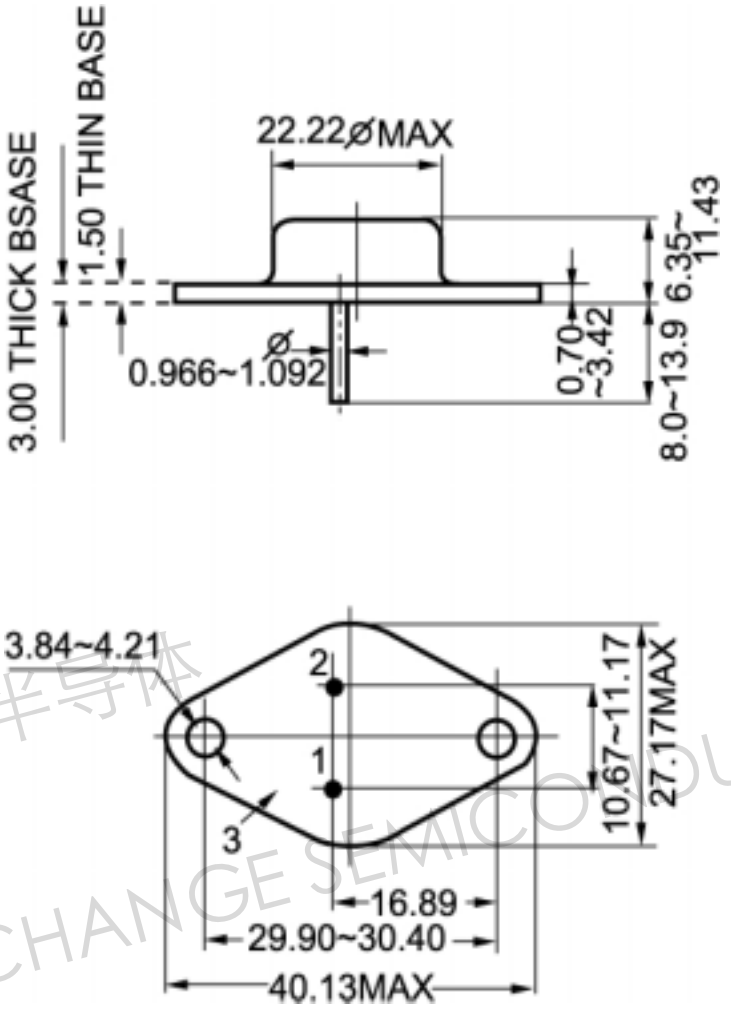

Fig.2 outline dimensions